



# ***HVR\_CCPD: Hybridization***



**A. Gaudiello**

INFN & Università di Genova

(Summary of the work done in Genova, Milano and Trento)

*March 14 2016*

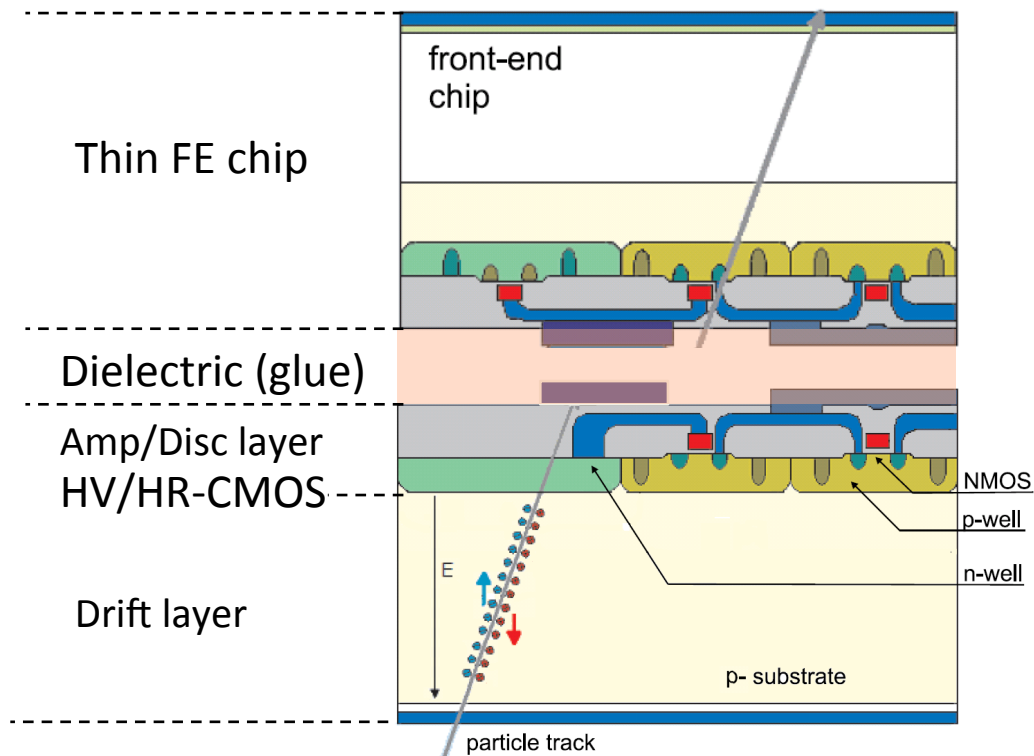
# Studies on Capacitive Couplings

The new 65 nm front-end chip, being developed by RD53 Collaboration, will be compatible with  **$50 \times 50 \mu\text{m}^2$  or  $25 \times 100 \mu\text{m}^2$  pixel size sensors.**

The smaller pixel sizes imply up to five times the bump density used in the current ATLAS Insertable B-Layer modules and consequently an order of **120 k pixels per chip.**

In next slides will be shown some studies done on:

- capacitive coupling for CMOS



# Studies on Capacitive Couplings

## Basic process

Spin SU-8 photoresist  
Pattern pillars by mask



Glue deposition



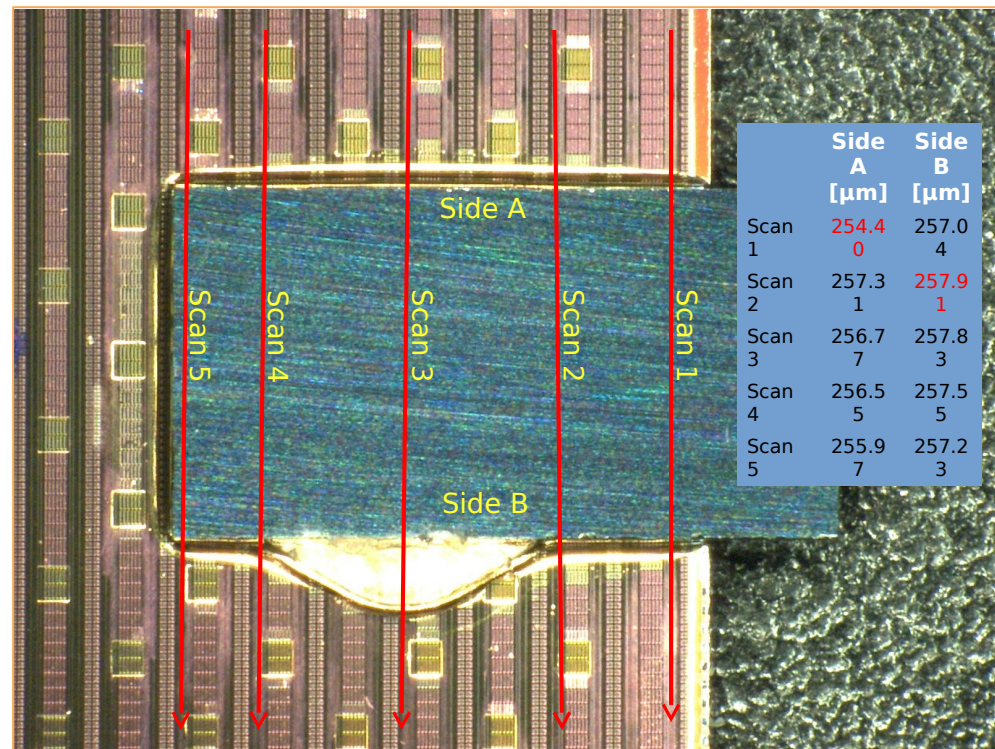
Align & pressure



Deposition of SU8  
photoresist by spinning

In 2014 and mid 2015 test on “in-house” hybridization

➡ Successful single chip assemblies and learnt on  
glue and SU8 deposition (spacers)



In picture: HV2FE-I

Now systematic test on large chips (FE-I4 size) and  
wafer process for pillars

# Studies on Capacitive Couplings

## Basic process

Spin SU-8 photoresist  
Pattern pillars by mask



Glue deposition



Align & pressure

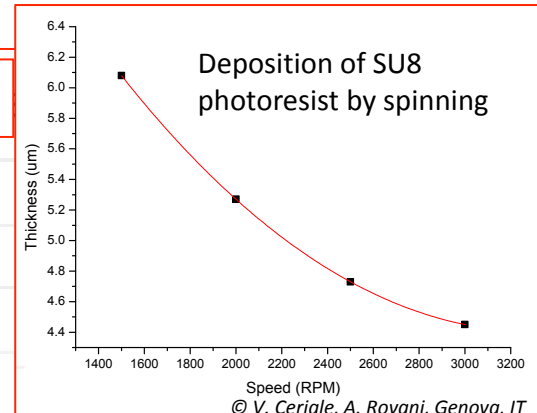
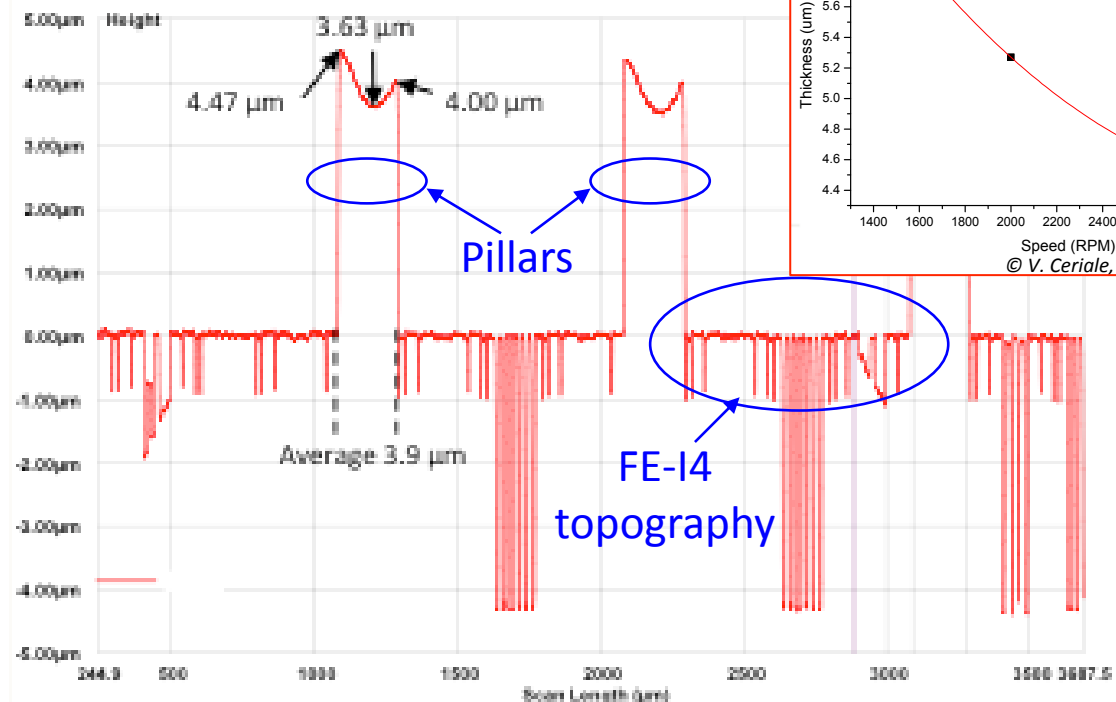


Deposition of SU8 photoresist by spinning

## Procedure for Controlled Glue Thickness

- Deposit uniform layer of SU8 photoresist on R/O chip wafer (or single chip) by spinning – tune for 5  $\mu\text{m}$  layer by controlling RPM speed
- Pattern pillars using lithographic process

## Profile of pillars on top of a FE-I4 chip





# Studies on Capacitive Couplings

In 2014 and mid 2015 test on “in-house” hybridization

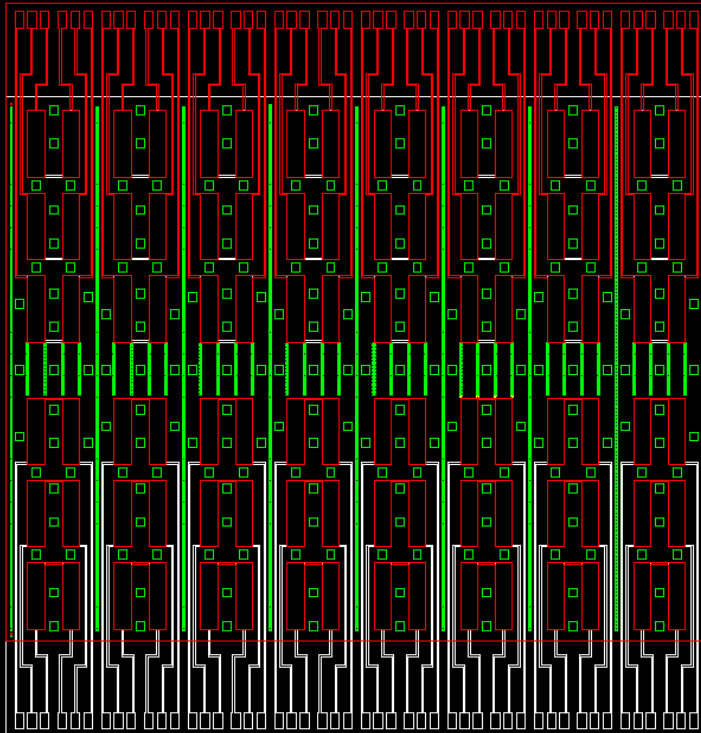
➡ Successful single chip assemblies and learnt on glue and SU8 deposition (spacers)

systematic test on large chips (FE-I4 size) and wafer process for pillars

**A batch of dummy wafer produces at FBK (Trento) with capacitive structures to test uniformity of glue thickness layer 6-inch wafers, 24-32 capacitors (3-7 pF) per chip**

## Basic process

Overlaid – Bottom metal + SU8 pillard + Top metal



photoresist by spinning

# Studies on Capacitive Couplings

## Basic process

Spin SU-8 photoresist  
Pattern pillars by mask



Glue deposition



Align & pressure



Deposition of SU8  
photoresist by spinning

In 2014 and mid 2015 test on “in-house” hybridization

➤ Successful single chip assemblies and learnt on glue and SU8 deposition (spacers)

Now systematic test on large chips (FE-I4 size) and wafer process for pillars

A batch of dummy wafer produces at FBK (Trento) with capacitive structures to test uniformity of glue thickness layer **6-inch wafers, 24-32 capacitors (3-7 pF) per chip**

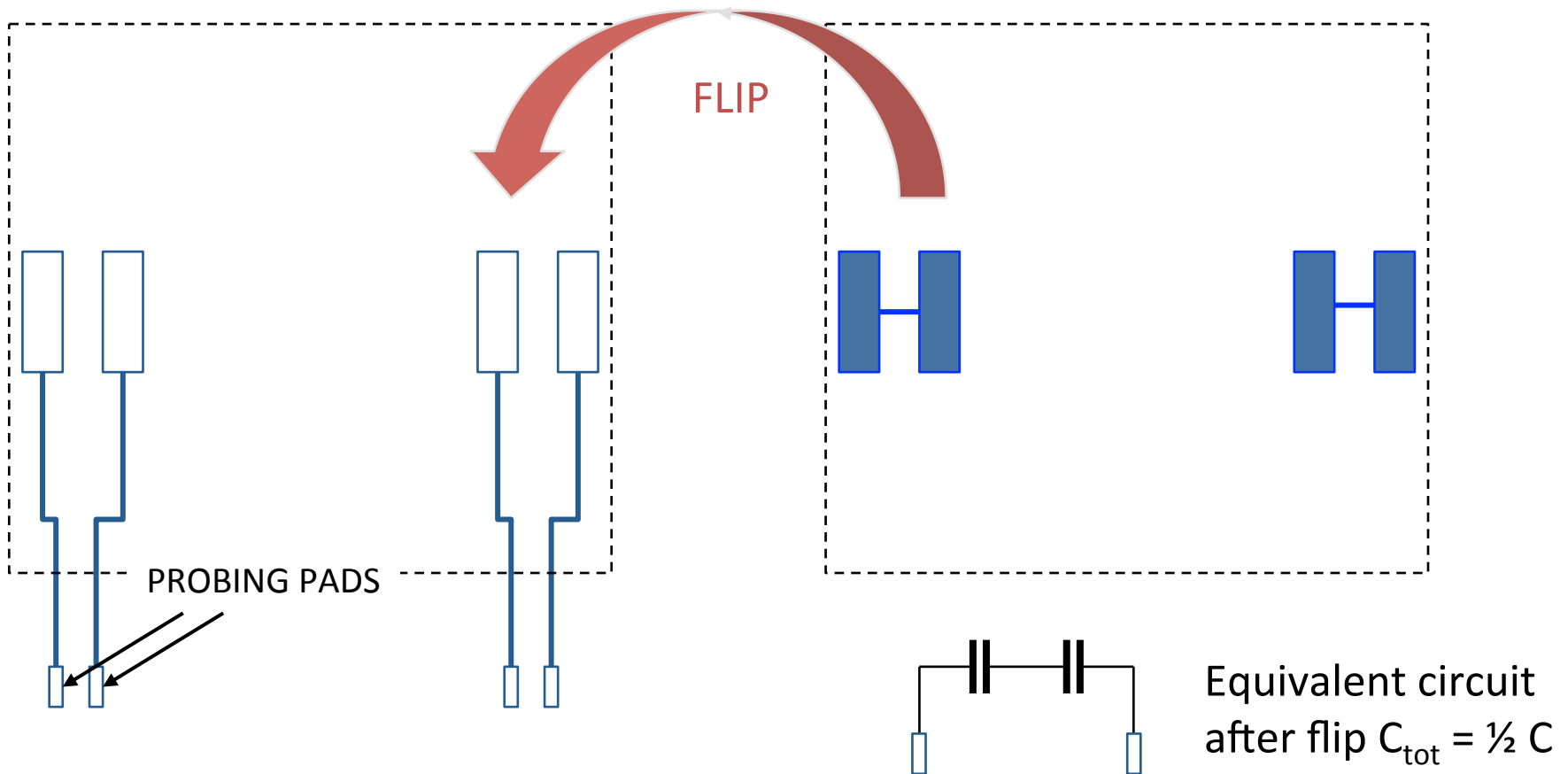
**The 6 wafers are at Selex together with pillar deposition mask – also 10 blank wafer provided to Selex to test SU8 spinning and photolithography – measurements of pillar uniformity will be done in Genova**

**PTA in Grenoble has been contacted for pillar deposition**  
**Flip-chip at Genova and other labs – thermal/UV glue curing (preliminary studies done)**

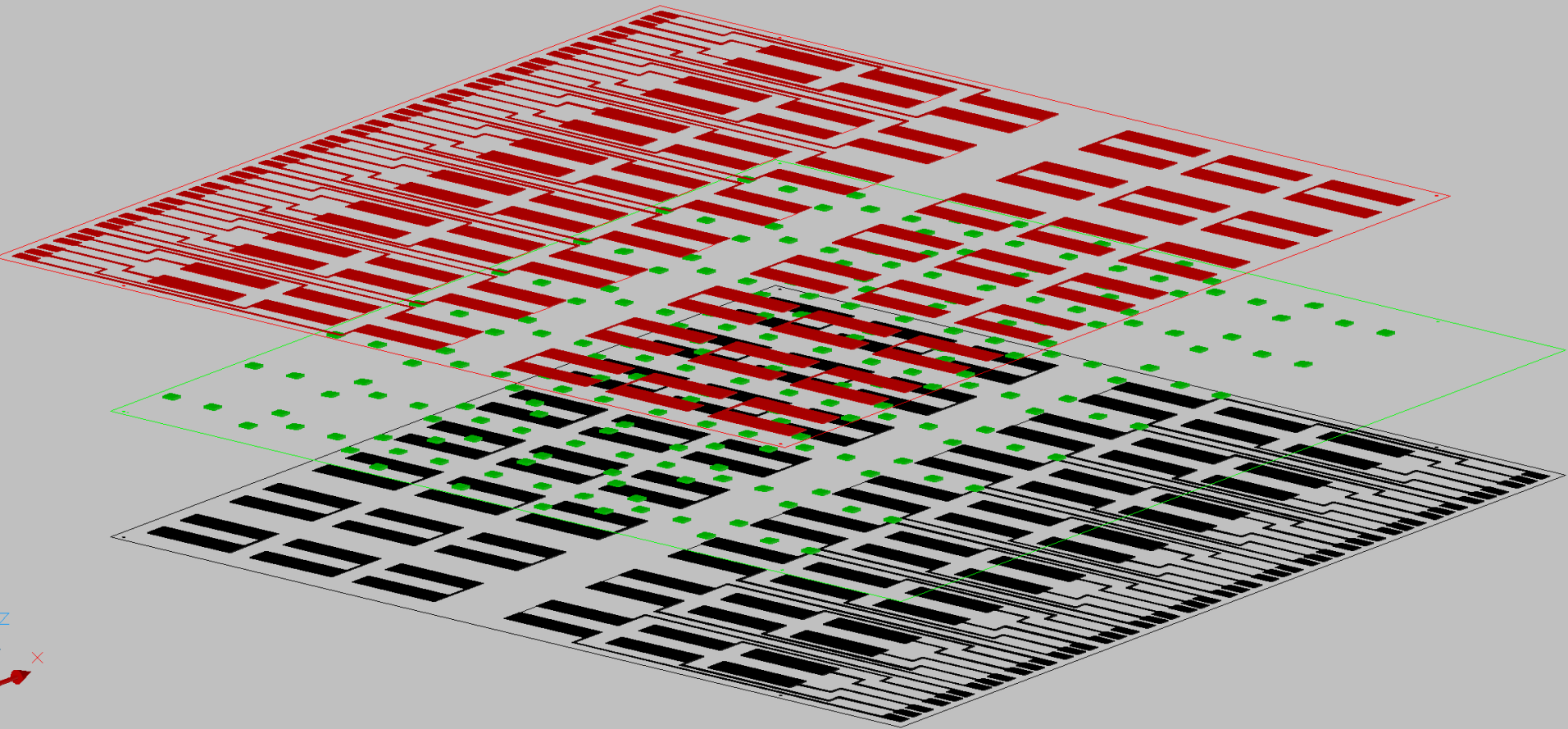
# Dummy Assembly

Test pillar and glue process on dummy wafers/chips

Design a 6-inch wafer with FE-I4 size dummies – place 32 (24) capacitors of 1 (2) mm<sup>2</sup> to test glue thickness uniformity over all surface



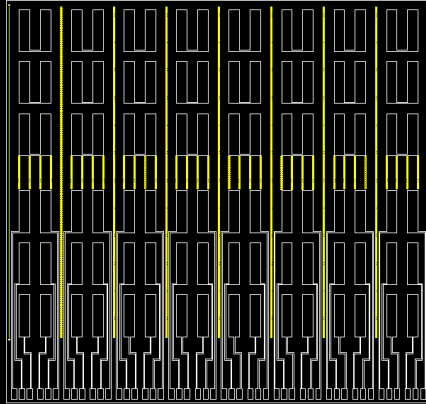
# *Dummy Assembly*



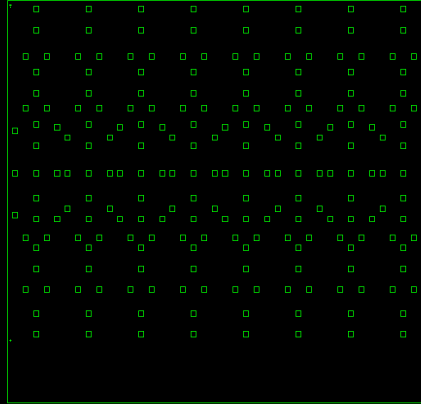


# Dummy Assembly

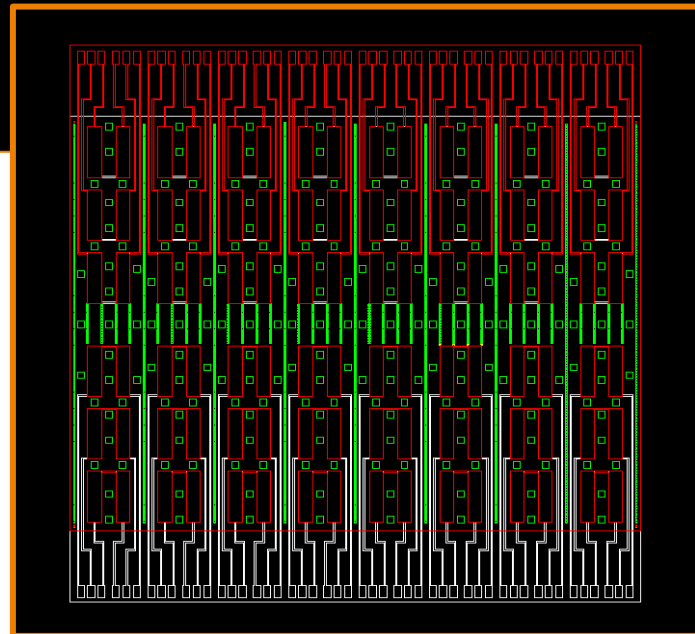
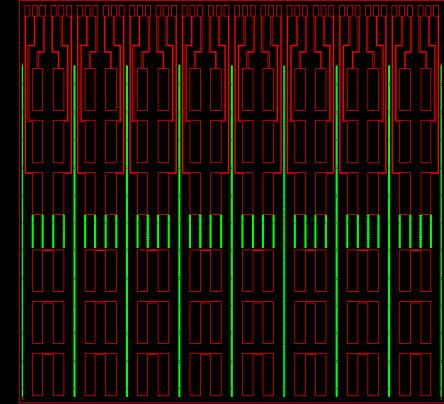
Bottom metal



SU8 pillars Mask

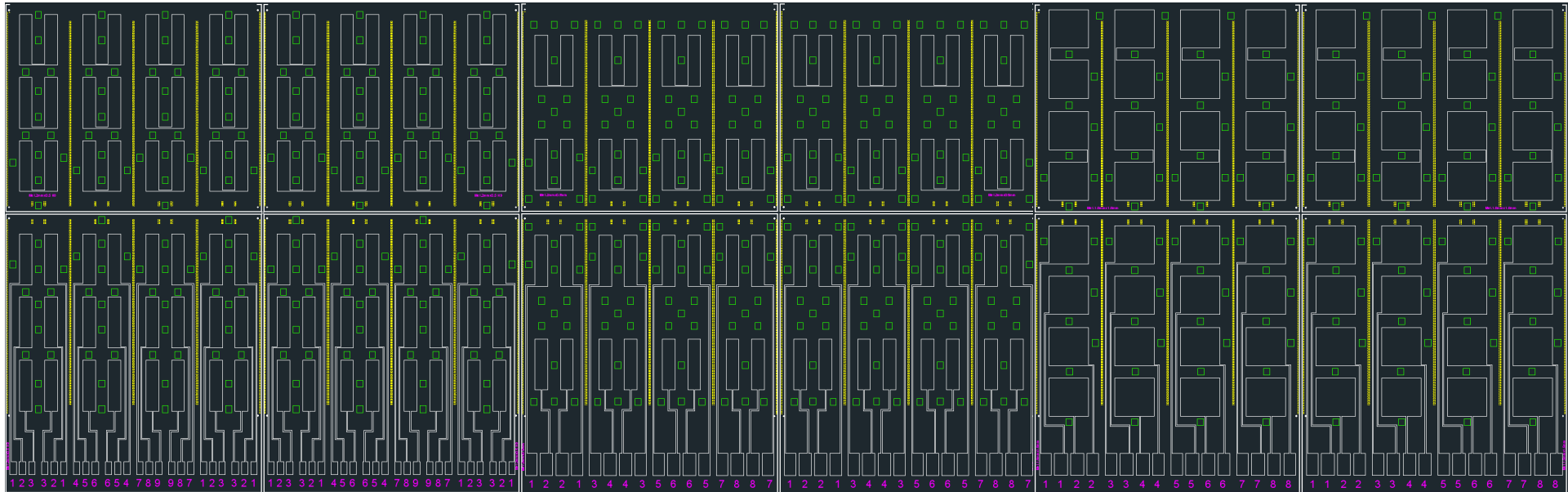


Top metal



# Dummy Assembly

## Different Layouts



### DESIGN 1

48 capacitors

3.6 fF @ 5 $\mu$  dielectric ( $\epsilon_r = 3.8$ )

### DESIGN 2

32 capacitors

3.6 fF @ 5 $\mu$  dielectric ( $\epsilon_r = 3.8$ )

### DESIGN 3

24 capacitors

~7 fF @ 5 $\mu$  dielectric ( $\epsilon_r = 3.8$ )

# Conclusions

## Capacitive Couplings:

- ✓ Good results of tests done on first lab prototypes
- ✓ **Dummy wafers for FE-I4 size tests produced**
  - ✓ Measurements will start as soon as the dummies will return from Selex